

IR2110L6

HIGH AND LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- Separate logic supply range from 5 to 20V
Logic and power ground $\pm 5V$ offset
- CMOS Schmitt-triggered inputs with pull-down
- Cycle by cycle edge-triggered shutdown logic
- Matched propagation delay for both channels
- Outputs in phase with inputs

Product Summary

V_{OFFSET}	600V max.
I_{O+/-}	2A / 2A
V_{OUT}	10 - 20V
t_{on/off} (typ.)	120 & 94 ns
Delay Matching	10 ns

Description

The IR2110L6 is a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

	Parameter	Min.	Max.	Units
V _B	High Side Floating Supply Voltage	-0.5	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	—	600	
V _{HO}	High Side Floating Output Voltage	V _S - 0.5	V _B + 0.5	
V _{CC}	Low Side Fixed Supply Voltage	-0.5	20	
V _{LO}	Low Side Output Voltage	-0.5	V _{CC} + 0.5	
V _{DD}	Logic Supply Voltage	-0.5	V _{SS} + 20	
V _{SS}	Logic Supply Offset Voltage	V _{CC} - 20	V _{CC} + 0.5	
V _{IN}	Logic Input Voltage (HIN, LIN & SD)	V _{SS} - 0.5	V _{DD} + 0.5	
dV _S /dt	Allowable Offset Supply Voltage Transient (Figure 2)	—	50	V/ns
P _D	Package Power Dissipation @ T _A ≤ +25°C	—	1.6	W
R _{θJA}	Thermal Resistance, Junction to Ambient	—	75	°C/W
T _J	Junction Temperature	-55	125	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	—	300	
	Weight	1.5 (typical)		g

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset ratings are tested with all supplies biased at 15V differential. Typical ratings at other bias conditions are shown in Figures 36 and 37.

	Parameter	Min.	Max.	Units
V _B	High Side Floating Supply Absolute Voltage	V _S + 10	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	-4	600	
V _{HO}	High Side Floating Output Voltage	V _S	V _B	
V _{CC}	Low Side Fixed Supply Voltage	10	20	
V _{LO}	Low Side Output Voltage	0	V _{CC}	
V _{DD}	Logic Supply Voltage	V _{SS} + 5	V _{SS} + 20	
V _{SS}	Logic Supply Offset Voltage	-5	5	
V _{IN}	Logic Input Voltage (H _{IN} , L _{IN} & S _D)	V _{SS}	V _{DD}	

V_{BIAS} (V_{CC}, V_{BS}, V_{DD}) = 15V, and V_{SS} = COM unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figure 3.

		Tj = 25°C			Tj = -55 to 125°C			
	Parameter	Min.	Typ.	Max.	Min.	Max.	Units	Test Conditions
t _{on}	Turn-On Propagation Delay	—	120	150	—	260	ns	V _S = 0V
t _{off}	Turn-Off Propagation Delay	—	94	125	—	220		V _S = 600V
t _{sd}	Shutdown Propagation Delay	—	110	140	—	235		V _S = 600V
t _r	Turn-On RiseTime	—	25	35	—	50		C _L = 1000pf
t _f	Turn-Off Fall Time	—	17	25	—	40		C _L = 1000pf
MT	Delay Matching, HS & LS Turn-On/Off	—	—	10	—	—		$ t_{\text{ton}} - t_{\text{ton}} / t_{\text{toff}} - t_{\text{toff}} $

Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS} , V_{DD}) = 15V, unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all three logic input pins: HIN, LIN and SD. The V_O and I_O parameters are referenced to COM or V_S and are applicable to the respective output pins: HO or LO.

	Parameter	Tj = 25°C			Tj = -55 to 125°C		Units	Test Conditions
		Min.	Typ.	Max.	Min.	Max.		
V_{IH}	Logic "1" Input Voltage	3.1	—	—	3.3	—	V	$V_{DD} = 5V$
		6.4	—	—	6.8	—		$V_{DD} = 10V$
		9.5	—	—	10	—		$V_{DD} = 15V$
		12.5	—	—	13.3	—		$V_{DD} = 20V$
V_{IL}	Logic "0" Input Voltage	—	—	1.8	—	1.7	V	$V_{DD} = 5V$
		—	—	3.8	—	3.6		$V_{DD} = 10V$
		—	—	6	—	5.7		$V_{DD} = 15V$
		—	—	8.3	—	7.9		$V_{DD} = 20V$
V_{OH}	High Level Output Voltage, $V_{BIAS} - V_O$	—	0.7	1.2	—	1.5	μA	$V_{IN} = V_{IH}$, $I_O = 0A$
V_{OL}	Low Level Output Voltage, V_O	—	—	0.1	—	0.1		$V_{IN} = V_{IH}$, $I_O = 0A$
I_{LK}	Offset Supply Leakage Current	—	—	50	—	250		$V_B = V_S = 600V$
I_{QBS}	Quiescent V_{BS} Supply Current	—	125	230	—	500		$V_{IN} = 0V$ or V_{DD}
I_{QCC}	Quiescent V_{CC} Supply Current	—	180	340	—	600		$V_{IN} = 0V$, or V_{DD}
I_{QDD}	Quiescent V_{DD} Supply Current	—	5	30	—	60		$V_{IN} = 0V$, or V_{DD}
I_{IN+}	Logic "1" Input Bias Current	—	15	40	—	70		$V_{IN} = V_{DD}$
I_{IN-}	Logic "0" Input Bias Current	—	—	1.0	—	10		$V_{IN} = 0V$
V_{BSUV+}	V_{BS} Supply Undervoltage Positive Going Threshold	7.5	8.6	9.7	—	—	V	
V_{BSUV-}	V_{BS} Supply Undervoltage Negative Going Threshold	7.0	8.2	9.4	—	—		
V_{CCUV+}	V_{CC} Supply Undervoltage Positive Going Threshold	7.4	8.5	9.6	—	—		
V_{CCUV-}	V_{CC} Supply Undervoltage Negative Going Threshold	7.0	8.2	9.4	—	—		
I_{O+}	Output High Short Circuit Pulsed Current	2.0	—	—	—	—	A	$V_O = 0V$, $V_{IN} = V_{DD}$ $PW \leq 10 \mu s$
I_{O-}	Output Low Short Circuit Pulsed Current	2.0	—	—	—	—		$V_O = 15V$, $V_{IN} = 0V$ $PW \leq 10 \mu s$

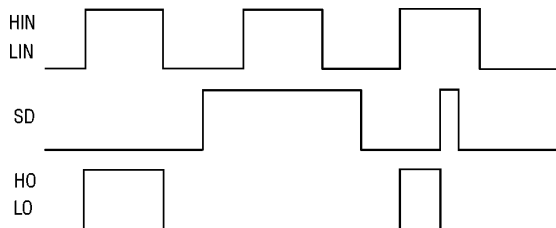


Figure 1. Input/Output Timing Diagram

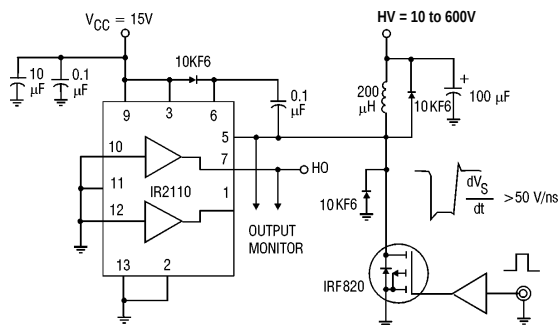


Figure 2. Floating Supply Voltage Transient Test Circuit

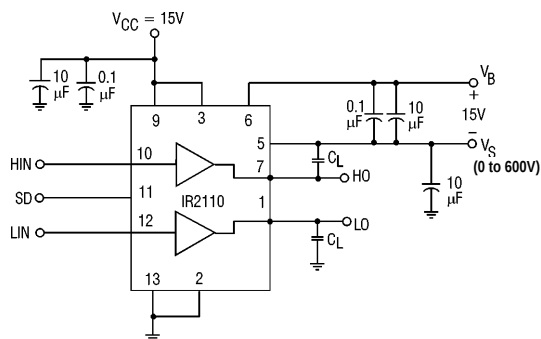


Figure 3. Switching Time Test Circuit

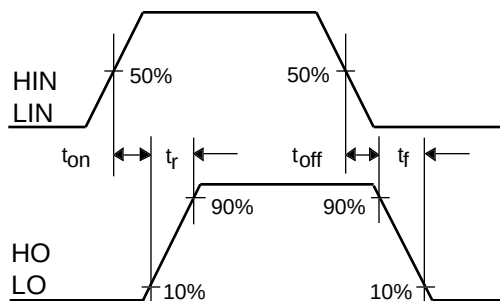


Figure 4. Switching Time Waveform Definition

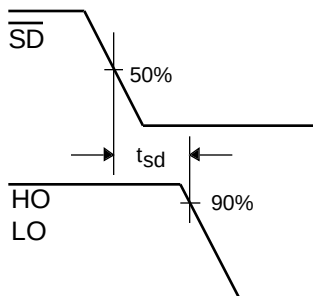


Figure 5. Shutdown Waveform Definitions

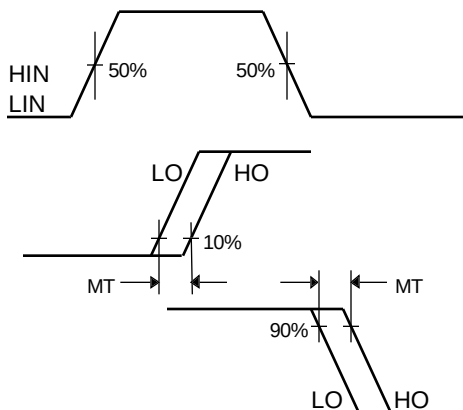


Figure 6. Delay Matching Waveform Definitions

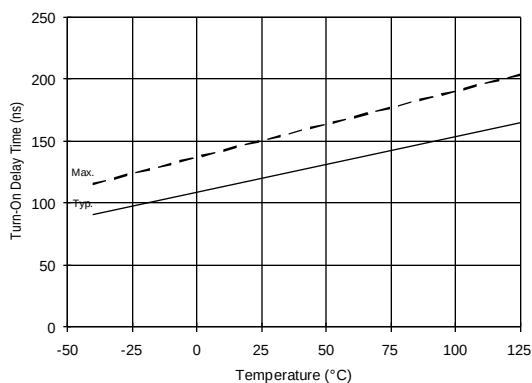


Figure 7A. Turn-On Time vs. Temperature

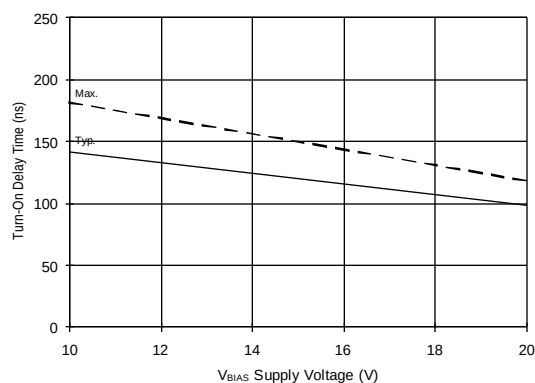


Figure 7B. Turn-On Time vs. Voltage

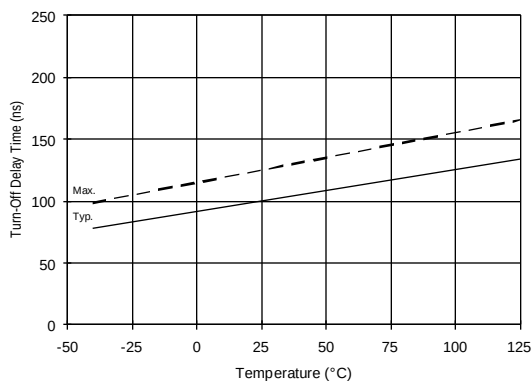


Figure 8A. Turn-Off Time vs. Temperature

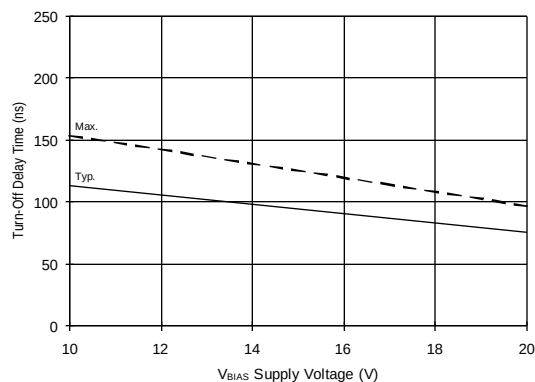


Figure 8B. Turn-Off Time vs. Voltage

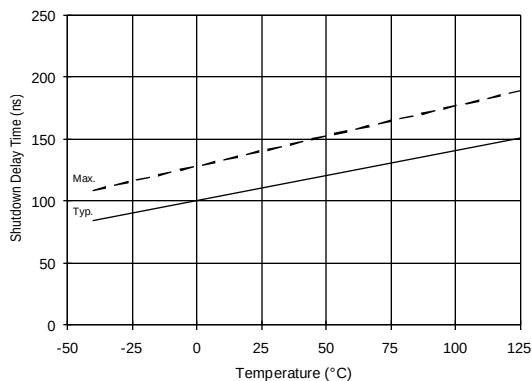


Figure 9A. Shutdown Time vs. Temperature

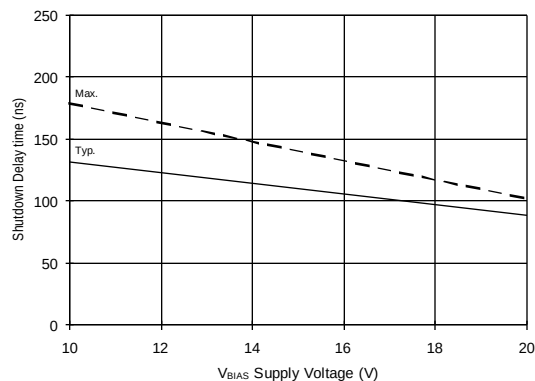


Figure 9B. Shutdown Time vs. Voltage

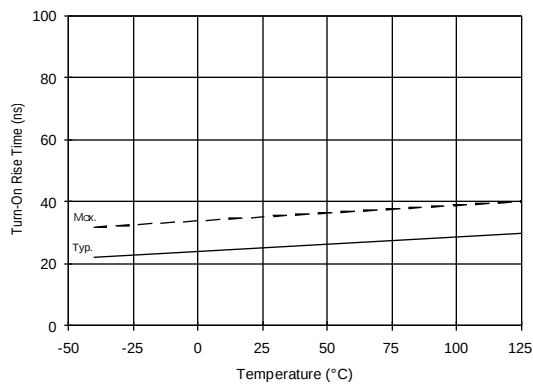


Figure 10A. Turn-On Rise Time vs. Temperature

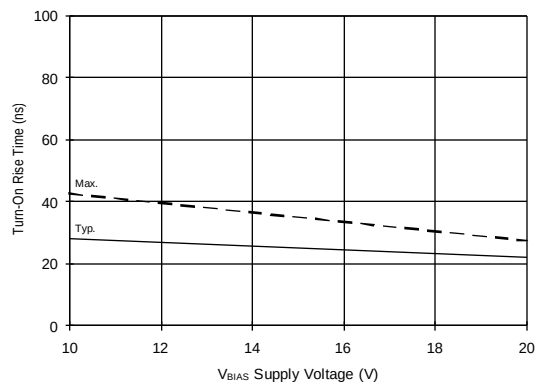


Figure 10B. Turn-On Rise Time vs. Voltage

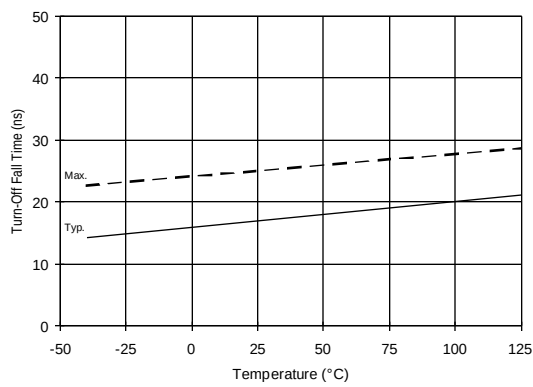


Figure 11A. Turn-Off Fall Time vs. Temperature

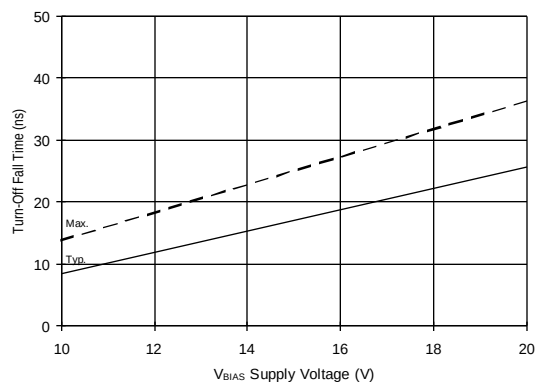


Figure 11B. Turn-Off Fall Time vs. Voltage

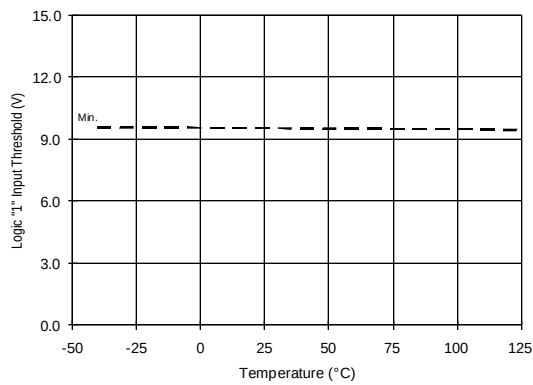


Figure 12A. Logic "1" Input Threshold vs. Temperature

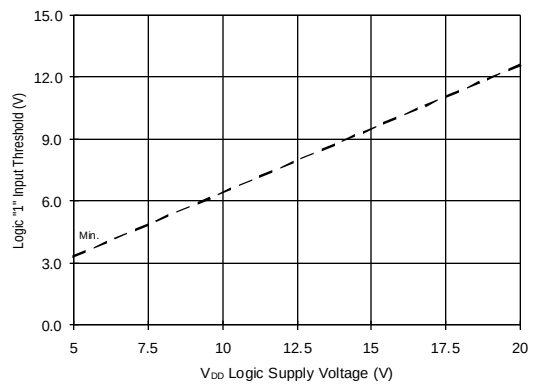


Figure 12B. Logic "1" Input Threshold vs. Voltage

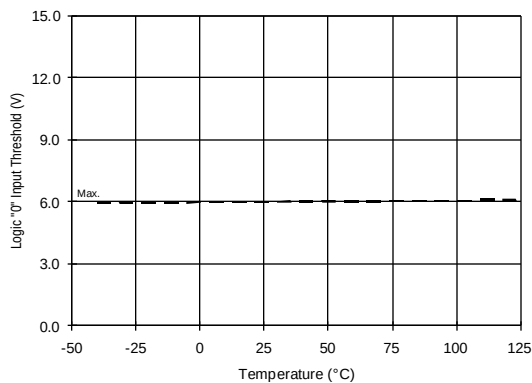


Figure 13A. Logic "0" Input Threshold vs. Temperature

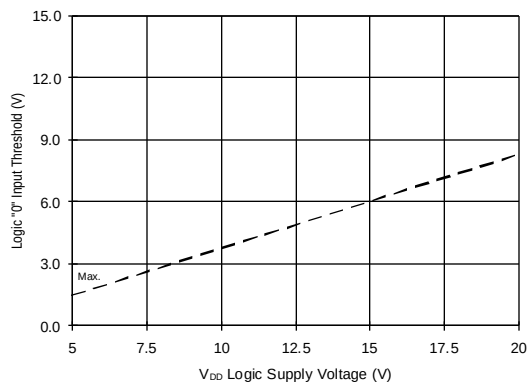


Figure 13B. Logic "0" Input Threshold vs. Voltage

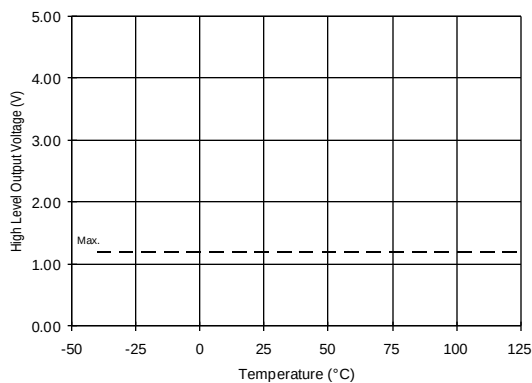


Figure 14A. High Level Output vs. Temperature

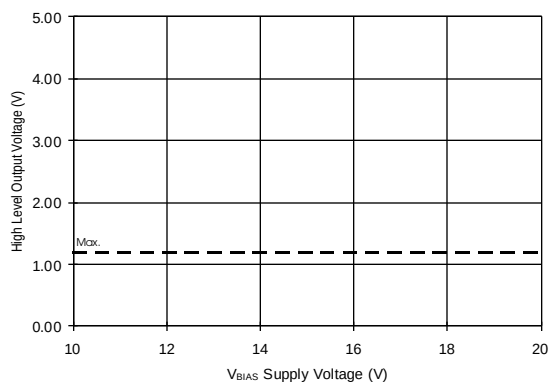


Figure 14B. High Level Output vs. Voltage

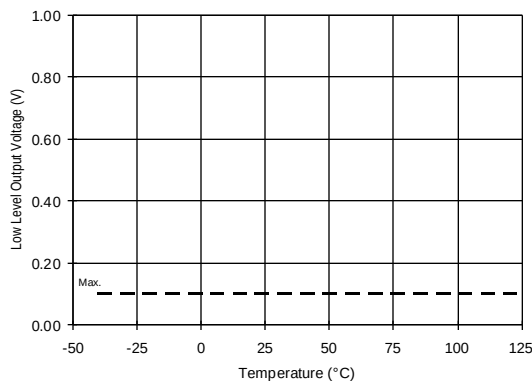


Figure 15A. Low Level Output vs. Temperature

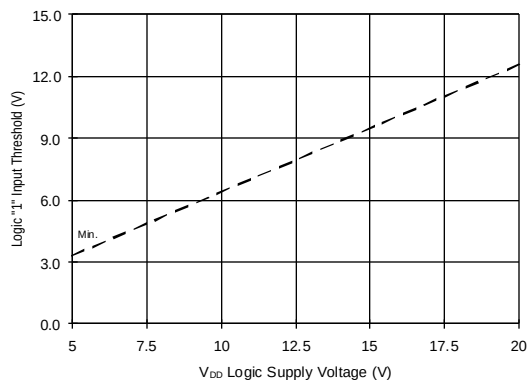


Figure 15B. Low Level Output vs. Voltage

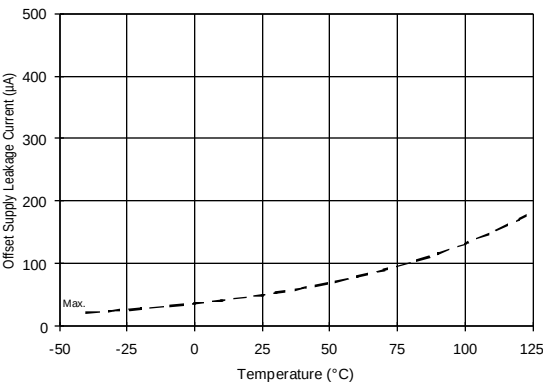


Figure 16A. Offset Supply Current vs. Temperature

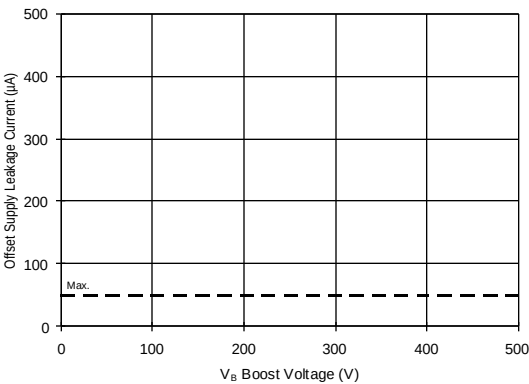


Figure 16B. Offset Supply Current vs. Voltage

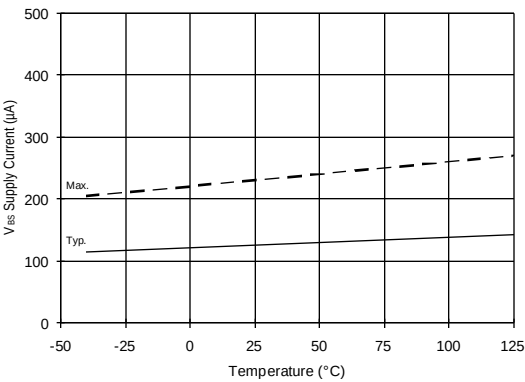


Figure 17A. V_{BS} Supply Current vs. Temperature

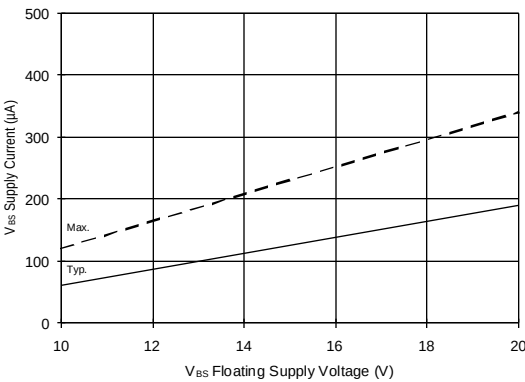


Figure 17B. V_{BS} Supply Current vs. Voltage

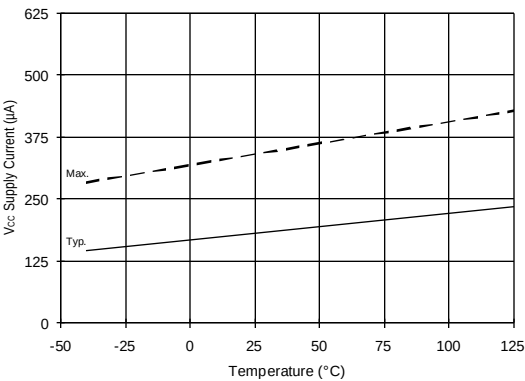


Figure 18A. V_{CC} Supply Current vs. Temperature

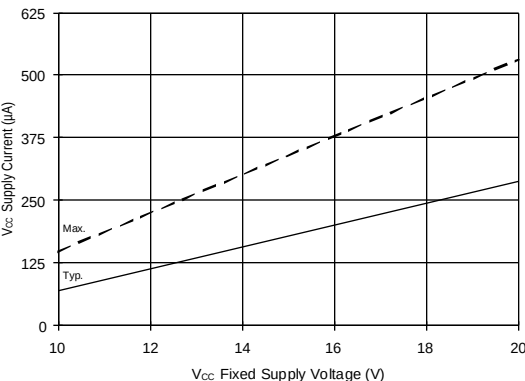


Figure 18B. V_{CC} Supply Current vs. Voltage

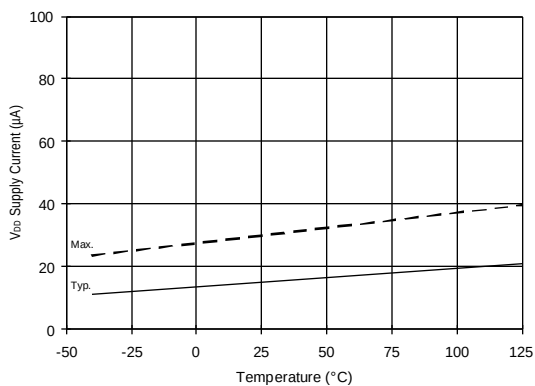


Figure 19A. V_{DD} Supply Current vs. Temperature

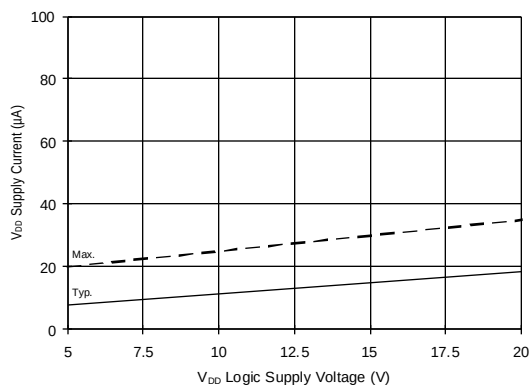


Figure 19B. V_{DD} Supply Current vs. Voltage

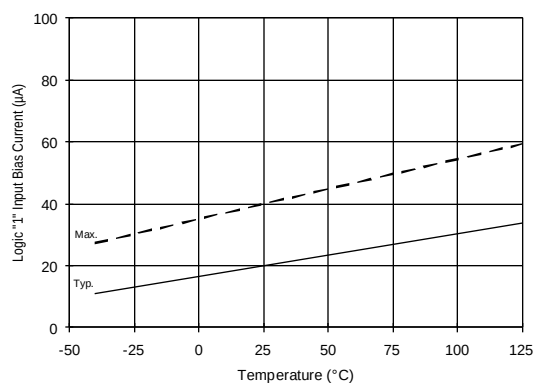


Figure 20A. Logic "1" Input Current vs. Temperature

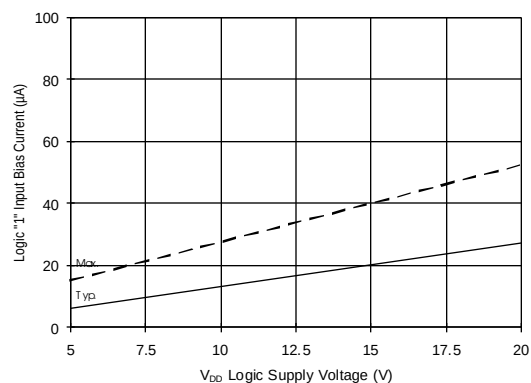


Figure 20B. Logic "1" Input Current vs. Voltage

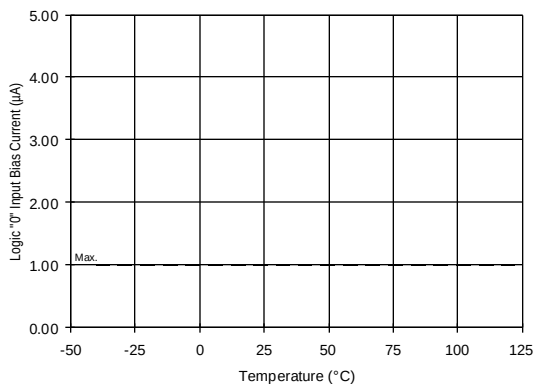


Figure 21A. Logic "0" Input Current vs. Temperature

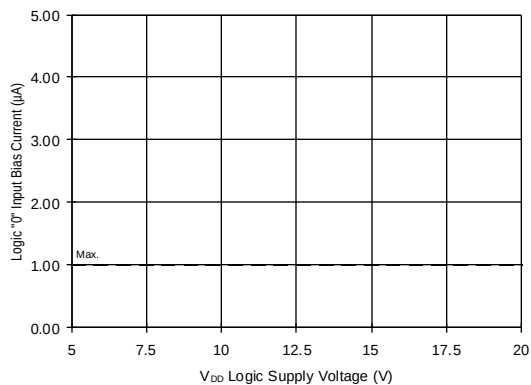


Figure 21B. Logic "0" Input Current vs. Voltage

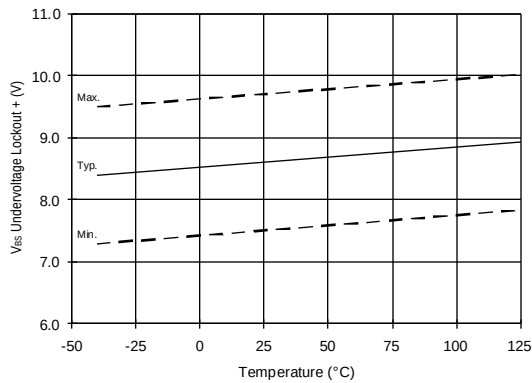


Figure 22. VBS Undervoltage (+) vs. Temperature

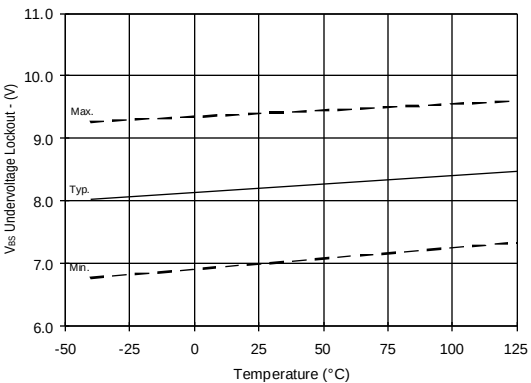


Figure 23. VBS Undervoltage (-) vs. Temperature

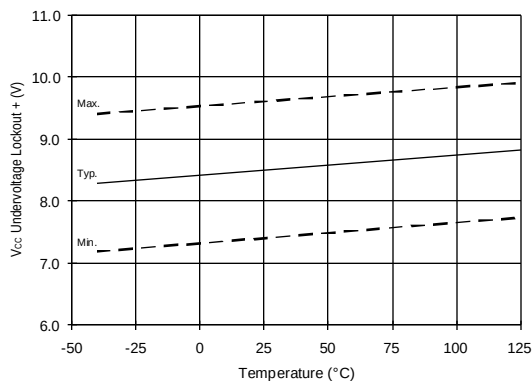


Figure 24. VCC Undervoltage (+) vs. Temperature

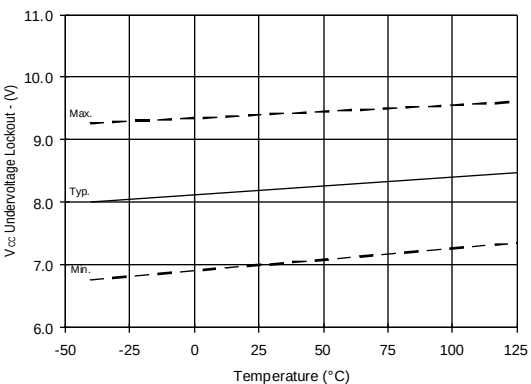


Figure 25. VCC Undervoltage (-) vs. Temperature

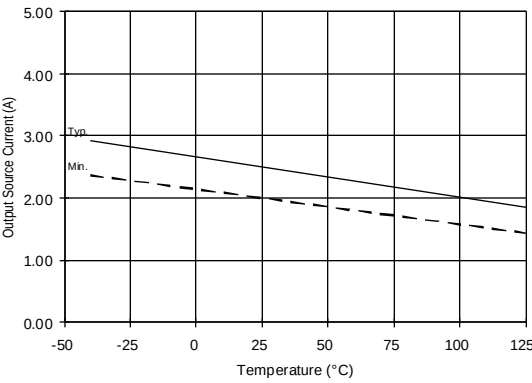


Figure 26A. Output Source Current vs. Temperature

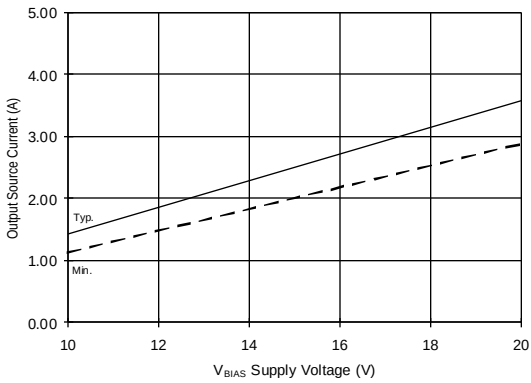


Figure 26B. Output Source Current vs. Voltage

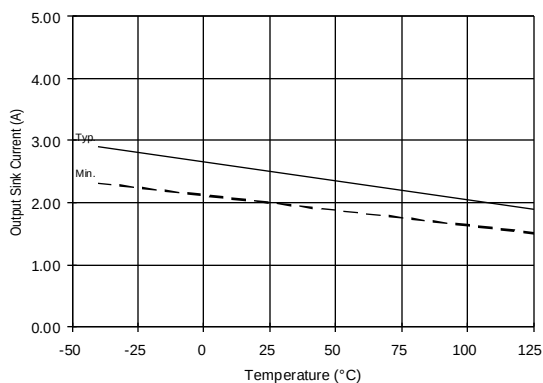


Figure 27A. Output Sink Current vs. Temperature

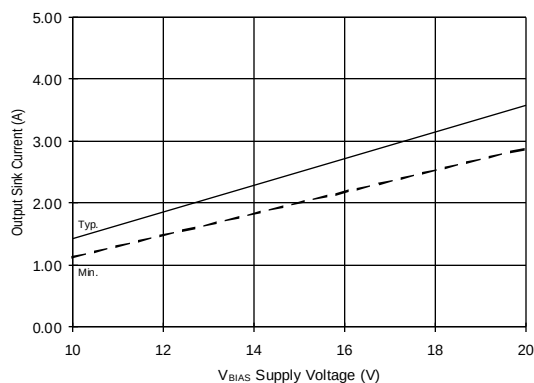


Figure 27B. Output Sink Current vs. Voltage

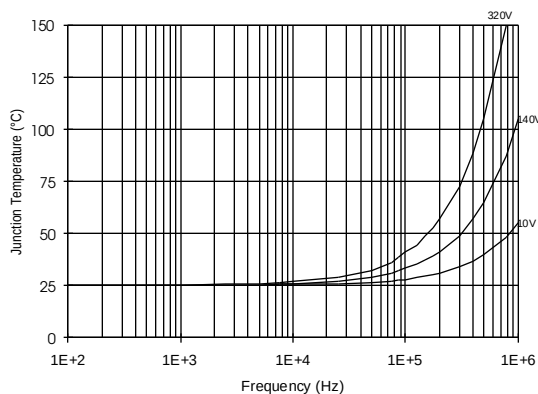


Figure 28. IR2110L6T_j vs. Frequency (IRFBC20)
 $R_{GATE} = 33\Omega$, $V_{CC} = 15V$

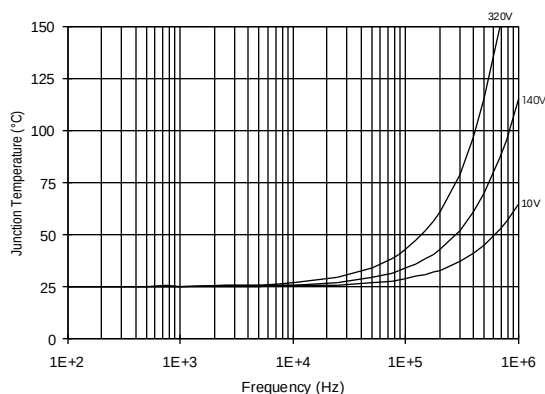


Figure 29. IR2110L6T_j vs. Frequency (IRFBC30)
 $R_{GATE} = 22\Omega$, $V_{CC} = 15V$

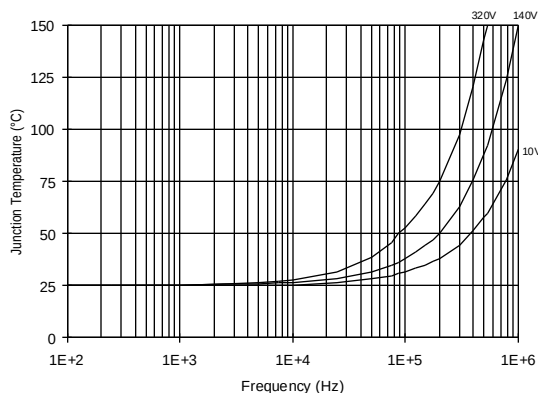


Figure 30. IR2110L6T_j vs. Frequency (IRFBC40)
 $R_{GATE} = 15\Omega$, $V_{CC} = 15V$

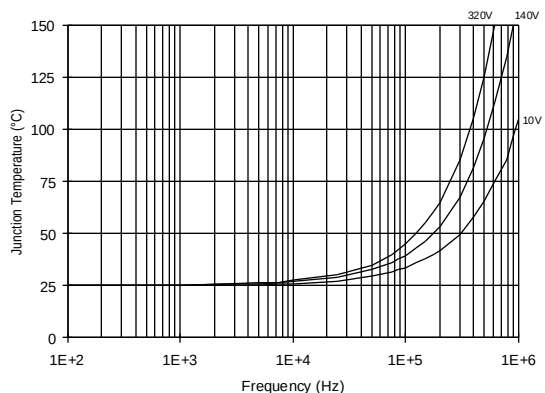


Figure 31. IR2110L6T_j vs. Frequency (IRFPE50)
 $R_{GATE} = 10\Omega$, $V_{CC} = 15V$

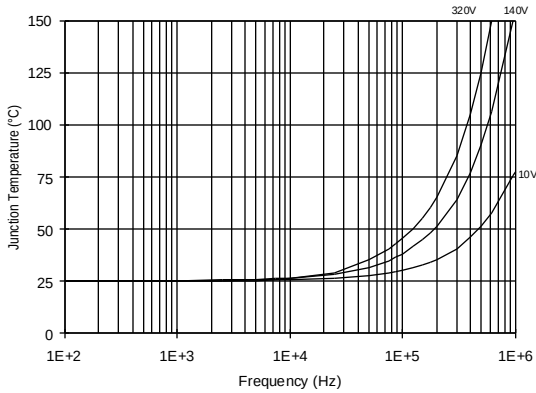


Figure 32. IR2110L6ST_J vs. Frequency (IRFBC20)
R_{GATE} = 33Ω, V_{CC} = 15V

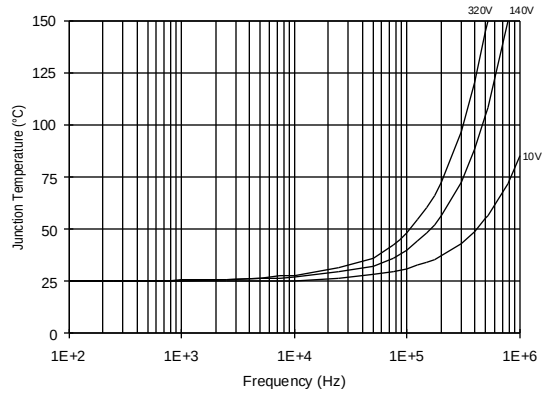


Figure 33. IR2110L6ST_J vs. Frequency (IRFBC30)
R_{GATE} = 22Ω, V_{CC} = 15V

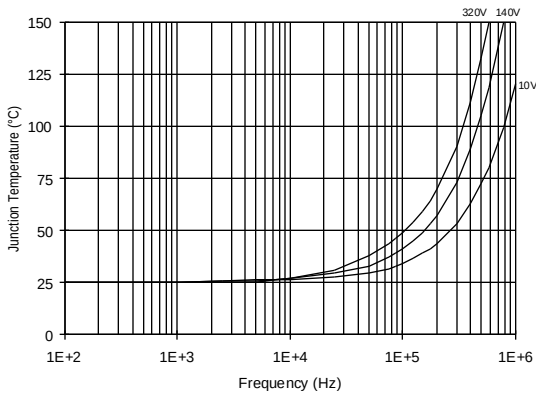


Figure 34. IR2110L6ST_J vs. Frequency (IRFBC40)
R_{GATE} = 15Ω, V_{CC} = 15V

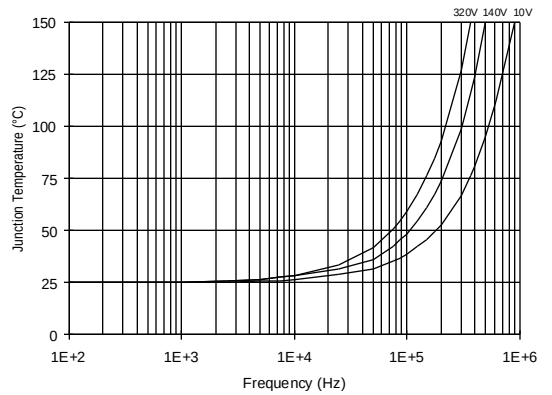


Figure 35. IR2110L6ST_J vs. Frequency (IRFPE50)
R_{GATE} = 10Ω, V_{CC} = 15V

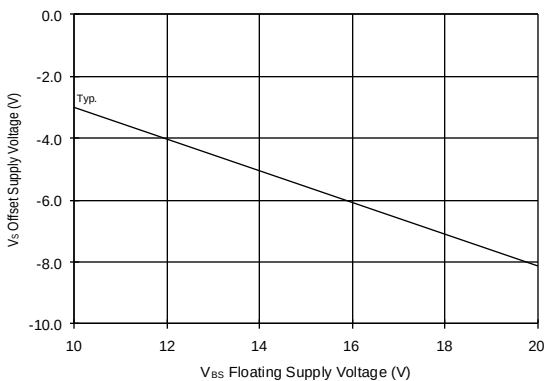


Figure 36. Maximum V_S Negative Offset vs. V_{BS} Supply Voltage

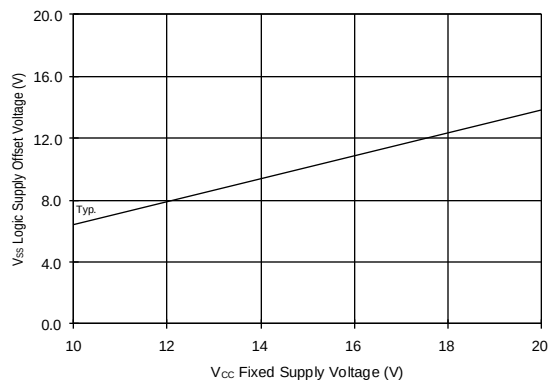
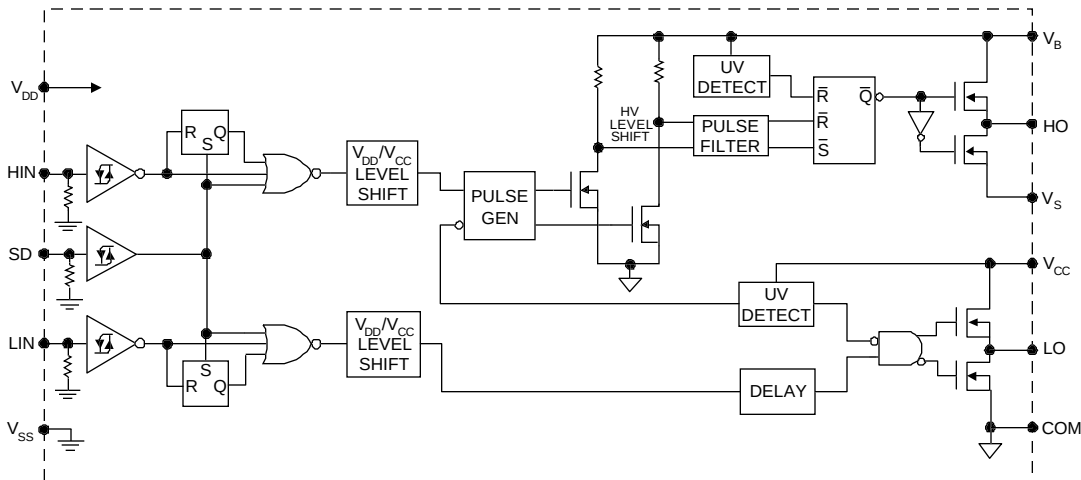


Figure 37. Maximum V_{SS} Positive Offset vs. V_{CC} Supply Voltage

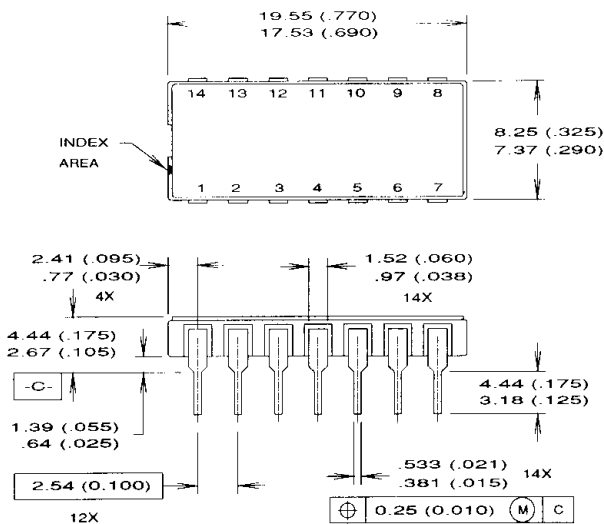
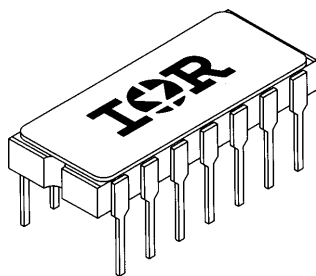
Functional Block Diagram



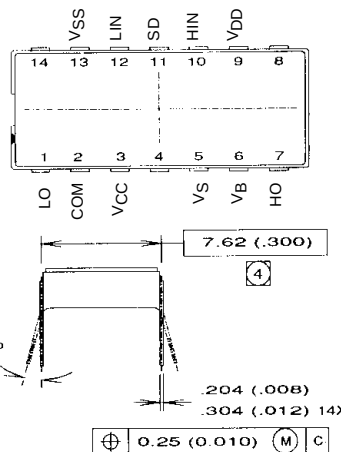
Lead Definitions

Lead	
Symbol	Description
V _{DD}	Logic supply
HIN	Logic input for high side gate driver output (HO), in phase
SD	Logic input for shutdown
LIN	Logic input for low side gate driver output (LO), in phase
V _{SS}	Logic ground
V _B	High side floating supply
HO	High side gate drive output
V _S	High side floating supply return
V _{CC}	Low side supply
LO	Low side gate drive output
COM	Low side return

Case Outline and Dimensions — MO-036AB



Pin Assignment



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION : INCH.

3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. DIMENSION IS TO CENTER OF LEADS WHEN FORMED PARALLEL.
5. OUTLINE CONFORMS TO JEDEC OUTLINE MO-036AB.

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IR Rectifier

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Data and specifications subject to change without notice.

6/96